NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into two groups, O and Y according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25^oC)

	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	V _{CBO} 35	
Collector Emitter Voltage	V _{CEO}	30	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current	Ι _c	800	mA
Base Current	Ι _Β	160	mA
Power Dissipation	P _{tot}	600	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	Ts	-55 to +150	°C







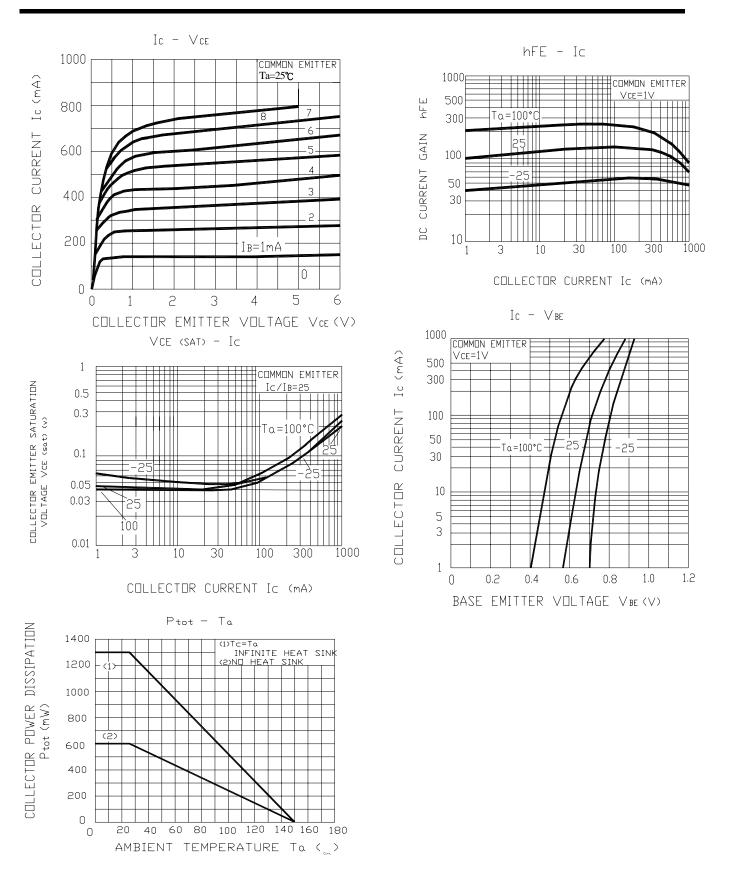
Characteristics at $T_{amb}=25$ °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at V _{CE} =1V, I _C =100mA					
Current Gain Group O	h_{FE}	100	-	200	-
Y	h_{FE}	160	-	320	-
at V _{CE} =1V, I _C =700mA	h _{FE}	35	-	-	-
Collector Cutoff Current					
at V _{CB} =35V	I _{CBO}	-	-	0.1	μA
Emitter Cutoff Current					
at V _{EB} =5V	I _{EBO}	-	-	0.1	μΑ
Collector Emitter Saturation Voltage					
at I _C =500mA, I _B =20mA	$V_{\text{CE(sat)}}$	-	-	0.5	V
Transition Frequency					
at V _{CE} =5V, I _C =10mA	f⊤	-	120	-	MHz
Base Emitter Voltage					
at $I_C=10mA$, $V_{CE}=1V$	V_{BE}	0.5	-	0.8	V
Collector Output Capacitance					
at V _{CB} =10V, f=1MHz	C _{OB}	-	13	-	pF
Collector Emitter Breakdown Voltage					
at I _c =10mA	V_{CEO}	30	-	-	V















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